International IƆR Rectifier

# IRF7331

HEXFET® Power MOSFET

- Ultra Low On-Resistance
- Dual N-Channel MOSFET
- Surface Mount
- Available in Tape & Reel

V_{DSS}	$R_{DS(on)}$ max (mΩ)	I_D
20V	30 @ V_{GS} = 4.5V	7.0A
	45 @ V_{GS} = 2.5V	5.6A

Description

These N-Channel HEXFET® power MOSFETs from International Rectifier utilize advanced processing techniques to achieve the extremely low on-resistance per silicon area. This benefit provides the designer with an extremely efficient device for use in battery and load management applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics and multiple-die capability making it ideal in a variety of power applications. With these improvements, multiple devices can be used in an application with dramatically reduced board space. The package is designed for vapor phase, infrared, or wave soldering techniques.

Top View   SO-8
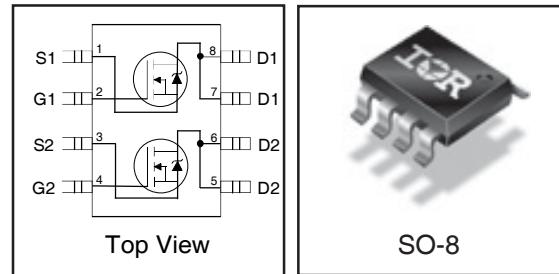
Absolute Maximum Ratings

	Parameter	Max.	Units
V_{DS}	Drain- Source Voltage	20	V
I_D @ T_A = 25°C	Continuous Drain Current, V_{GS} @ 4.5V	7.0	
I_D @ T_A= 70°C	Continuous Drain Current, V_{GS} @ 4.5V	5.5	A
I_{DM}	Pulsed Drain Current ①	28	
P_D @T_A = 25°C	Power Dissipation ③	2.0	W
P_D @T_A = 70°C	Power Dissipation③	1.3	
	Linear Derating Factor	16	mW/°C
V_{GS}	Gate-to-Source Voltage	± 12	V
T_J, T_{STG}	Junction and Storage Temperature Range	-55 to + 150	°C

Thermal Resistance

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JL}$	Junction-to-Drain Lead	——	42	
$R_{\theta JA}$	Junction-to-Ambient ③	——	62.5	°C/W

1

07/09/08

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	20	——	——	V	V_{GS} = 0V, I_D = 250µA
$\Delta V_{(BR)DSS}/\Delta T_J$	Breakdown Voltage Temp. Coefficient	——	0.013	——	V/°C	Reference to 25°C, I_D = 1mA
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	——	——	30	mΩ	V_{GS} = 4.5V, I_D = 7.0A ②
		——	——	45		V_{GS} = 2.5V, I_D = 5.6A ②
$V_{GS(th)}$	Gate Threshold Voltage	0.6	——	1.2	V	V_{DS} = V_{GS}, I_D = 250µA
g_{fs}	Forward Transconductance	14	——	——	S	V_{DS} = 10V, I_D = 7.0A
I_{DSS}	Drain-to-Source Leakage Current	——	——	1.0	µA	V_{DS} = 16V, V_{GS} = 0V
		——	——	25		V_{DS} = 16V, V_{GS} = 0V, T_J = 70°C
I_{GSS}	Gate-to-Source Forward Leakage	——	——	100	nA	V_{GS} = 12V
	Gate-to-Source Reverse Leakage	——	——	-100		V_{GS} = -12V
Q_g	Total Gate Charge	——	13	20		I_D = 7.0A
Q_{gs}	Gate-to-Source Charge	——	3.7	——	nC	V_{DS} = 10V
Q_{gd}	Gate-to-Drain ("Miller") Charge	——	2.1	——		V_{GS} = 4.5V
$t_{d(on)}$	Turn-On Delay Time	——	7.6	——		V_{DD} = 10V ②
t_r	Rise Time	——	22	——	ns	I_D = 1.0A
$t_{d(off)}$	Turn-Off Delay Time	——	110	——		R_G = 53Ω
t_f	Fall Time	——	50	——		V_{GS} = 4.5V
C_{iss}	Input Capacitance	——	1340	——		V_{GS} = 0V
C_{oss}	Output Capacitance	——	170	——	pF	V_{DS} = 16V
C_{rss}	Reverse Transfer Capacitance	——	120	——		f = 1.0MHz

Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	——	———	2.0	A	MOSFET symbol showing the integral reverse p-n junction diode.
I_{SM}	Pulsed Source Current (Body Diode) ①	——	———	28		
V_{SD}	Diode Forward Voltage	——	——	1.2	V	T_J = 25°C, I_S = 2.0A, V_{GS} = 0V ②
t_{rr}	Reverse Recovery Time	——	31	47	ns	T_J = 25°C, I_F = 2.0A
Q_{rr}	Reverse Recovery Charge	——	15	23	nC	di/dt = 100A/µs ②
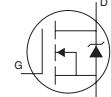
Notes:

① Repetitive rating; pulse width limited by
   max. junction temperature.

③ Surface mounted on 1 in square Cu board

② Pulse width ≤ 400µs; duty cycle ≤ 2%.
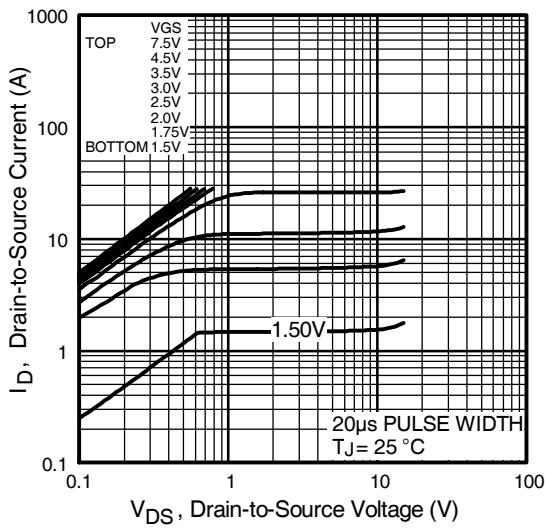
**Fig 1.** Typical Output Characteristics
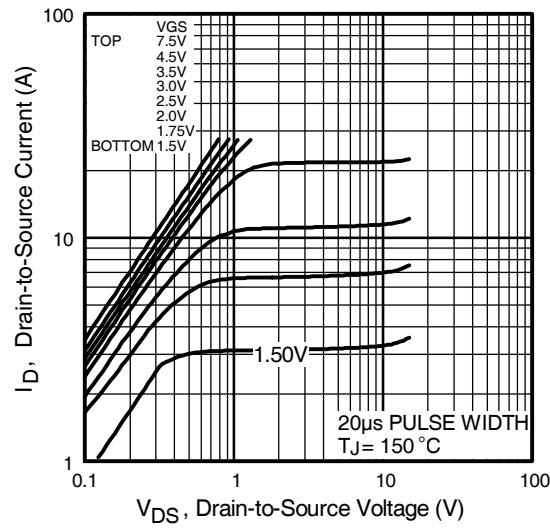
**Fig 2.** Typical Output Characteristics
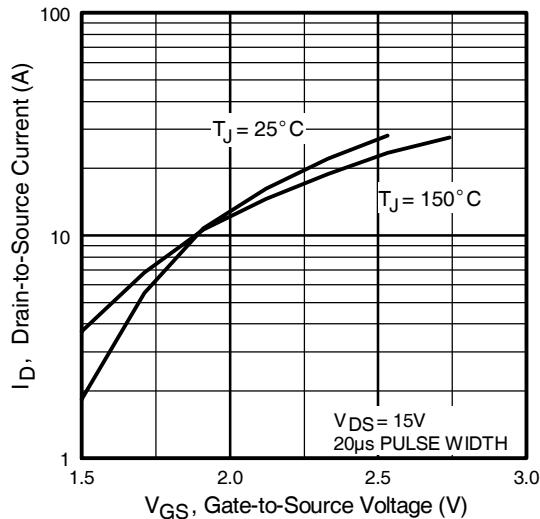

**Fig 3.** Typical Transfer Characteristics
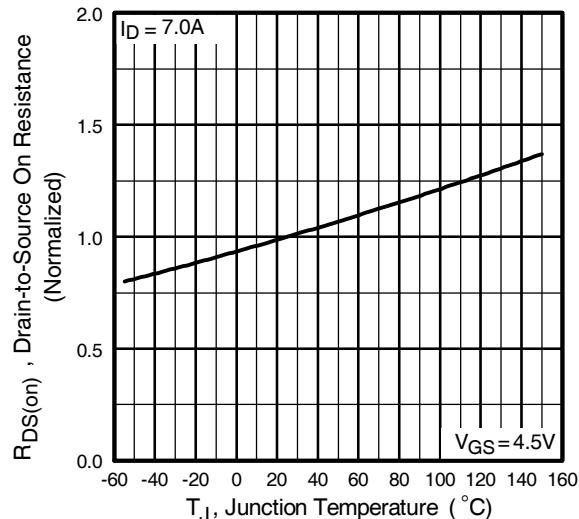
**Fig 4.** Normalized On-Resistance
Vs. Temperature

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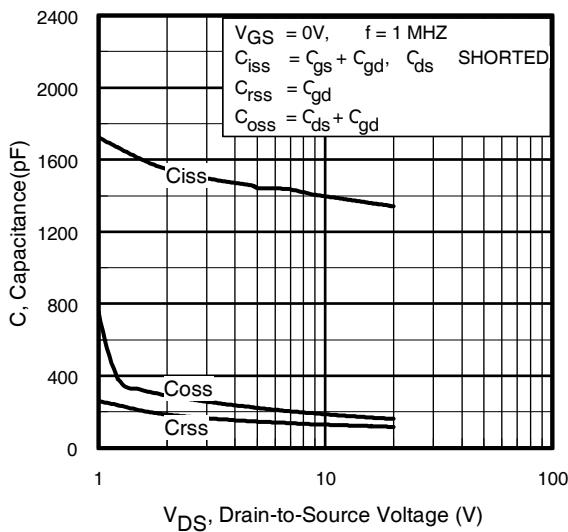
**Fig 5.** Typical Capacitance Vs. Drain-to-Source Voltage
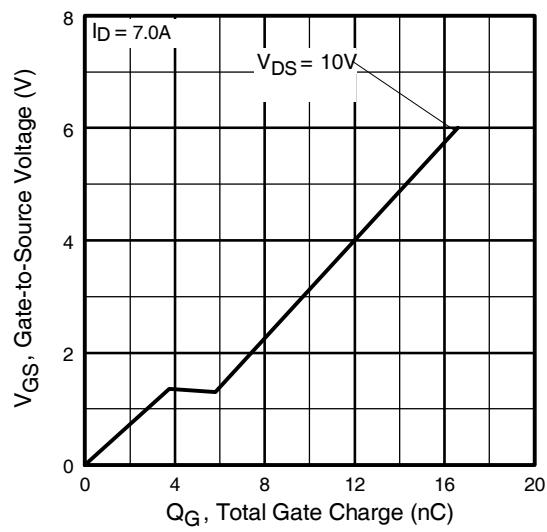
Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage
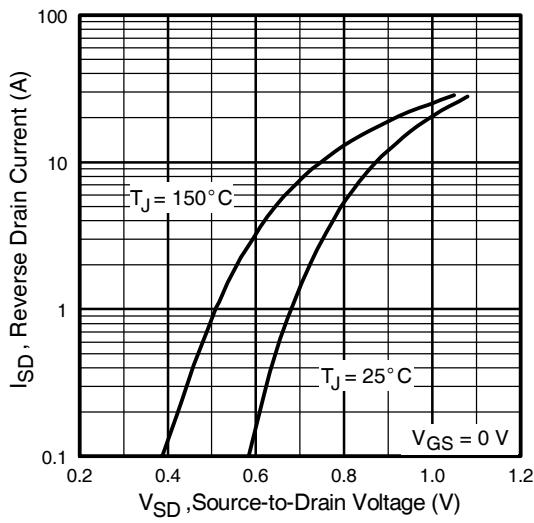

**Fig 7.** Typical Source-Drain Diode Forward Voltage
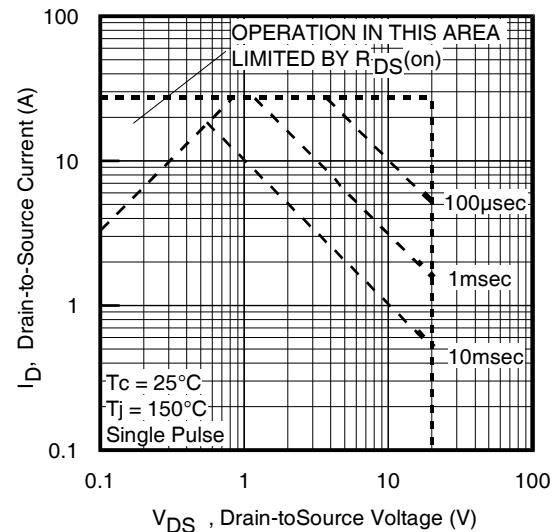

Fig 8. Maximum Safe Operating Area
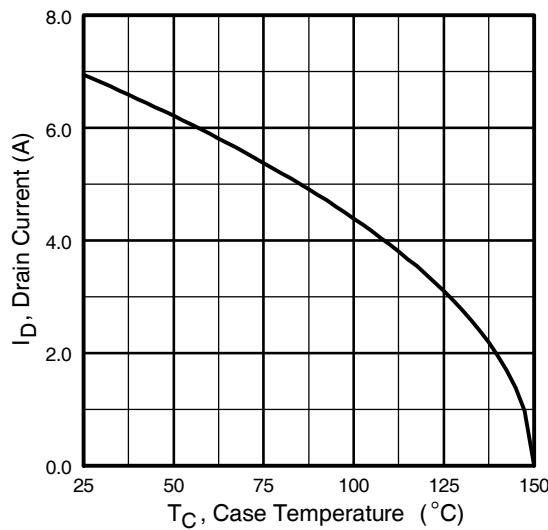
Fig 9. Maximum Drain Current Vs.
Case Temperature
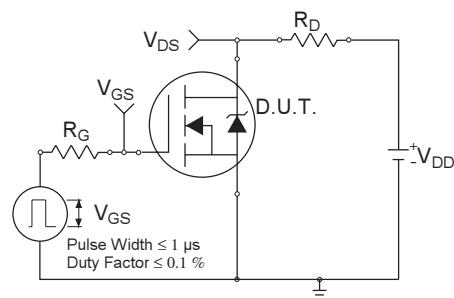
Fig 10a. Switching Time Test Circuit

Pulse Width ≤ 1 µs
Duty Factor ≤ 0.1 %

$t_{d(on)}$ t_r $t_{d(off)}$ t_f
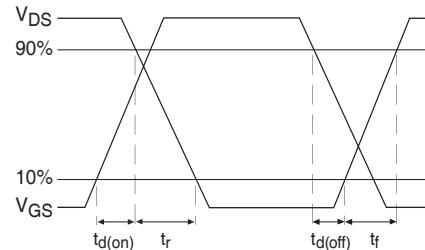
Fig 10b. Switching Time Waveforms

SINGLE PULSE
(THERMAL RESPONSE)

Notes:
1. Duty factor D = t_1 / t_2
2. Peak $T_J = P_{DM} \times Z_{thJA} + T_A$

t_1, Rectangular Pulse Duration (sec)
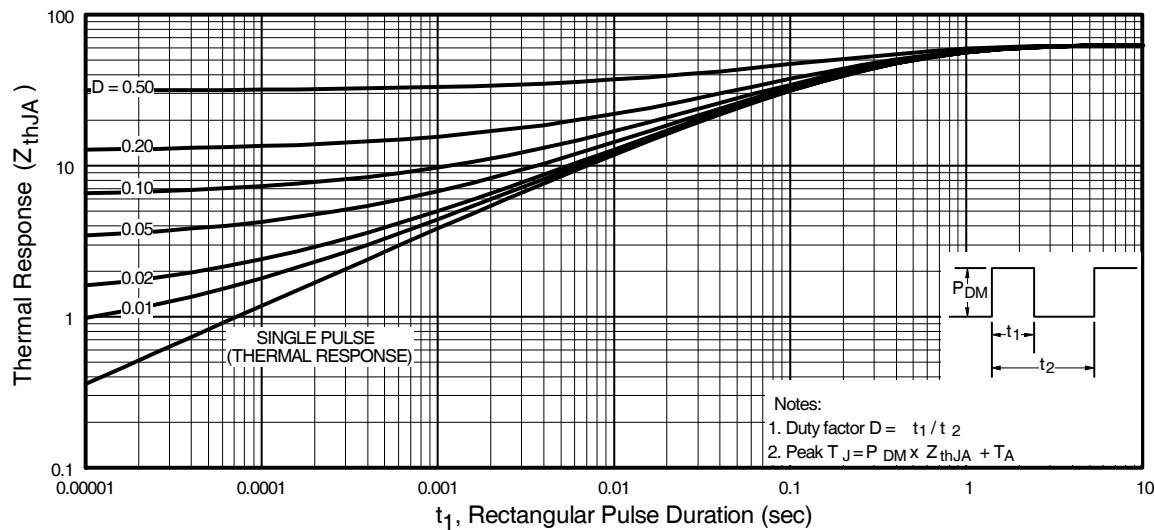
Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

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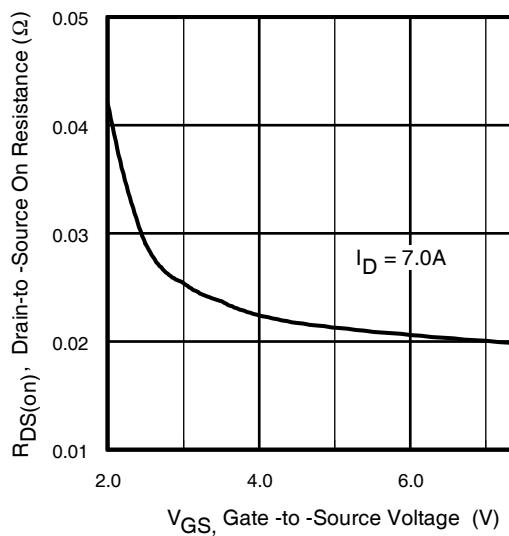
Fig 12. Typical On-Resistance Vs. Gate Voltage
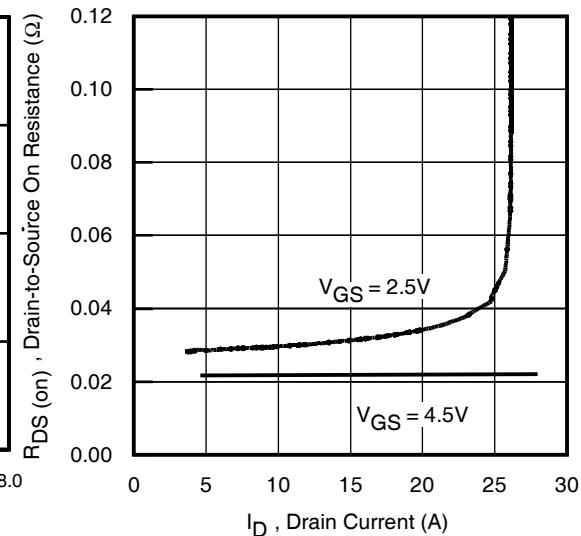

Fig 13. Typical On-Resistance Vs. Drain Current
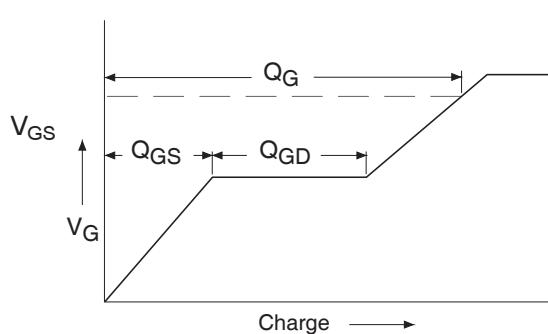
Fig 14a. Basic Gate Charge Waveform
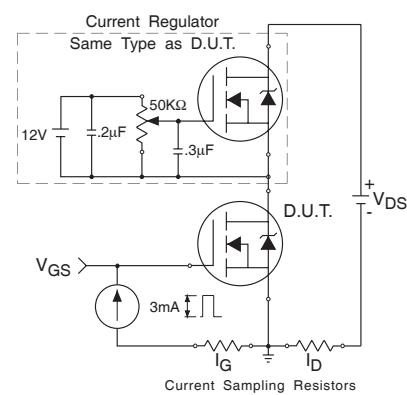
Fig 14b. Gate Charge Test Circuit

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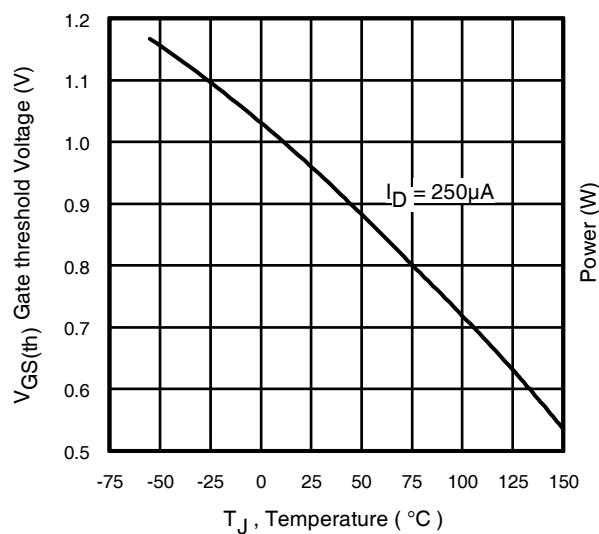
Fig 15. Typical Vgs(th) Vs.
Junction Temperature
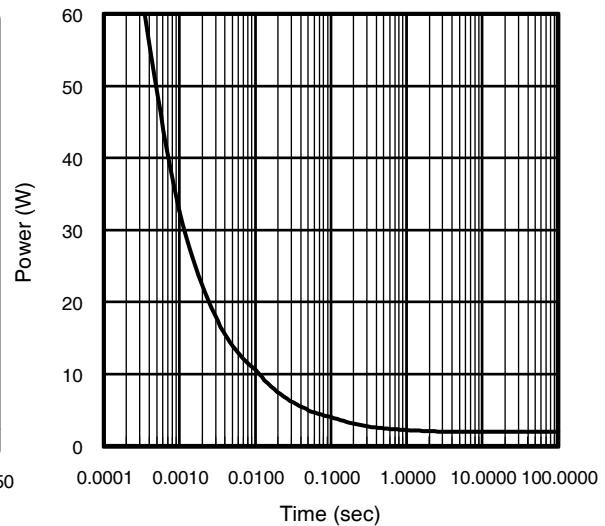

Fig 16. Typical Power Vs. Time

SO-8 Package Outline(Mosfet & Fetky)

Dimensions are shown in milimeters (inches)
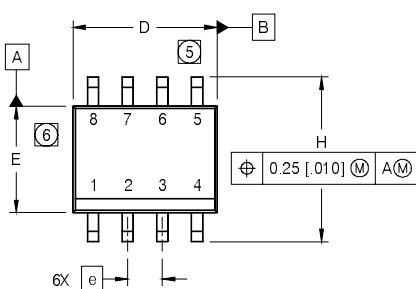
| DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.0532	.0688	1.35	1.75
A1	.0040	.0098	0.10	0.25
b	.013	.020	0.33	0.51
c	.0075	.0098	0.19	0.25
D	.189	.1968	4.80	5.00
E	.1497	.1574	3.80	4.00
e	.050 BASIC		1.27 BASIC	
e1	.025 BASIC		0.635 BASIC	
H	.2284	.2440	5.80	6.20
K	.0099	.0196	0.25	0.50
L	.016	.050	0.40	1.27
y	0°	8°	0°	8°
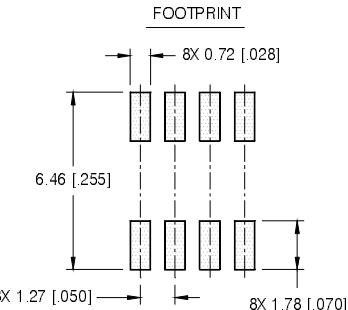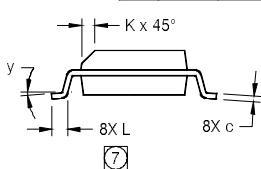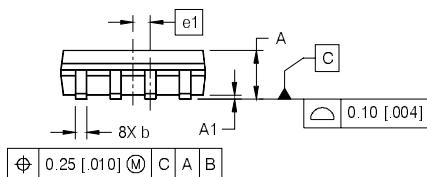
NOTES:
1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: MILLIMETER
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].
4. OUTLINE CONFORMS TO JEDEC OUTLINE MS-012AA.
5. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
   MOLD PROTRUSIONS NOT TO EXCEED 0.15 [.006].
6. DIMENSION DOES NOT INCLUDE MOLD PROTRUSIONS.
   MOLD PROTRUSIONS NOT TO EXCEED 0.25 [.010].
7. DIMENSION IS THE LENGTH OF LEAD FOR SOLDERING TO
   A SUBSTRATE.

FOOTPRINT

8X 0.72 [.028]

6.46 [.255]

3X 1.27 [.050]

8X 1.78 [.070]

SO-8 Part Marking Information

EXAMPLE: THIS IS AN IRF7101 (MOSFET)
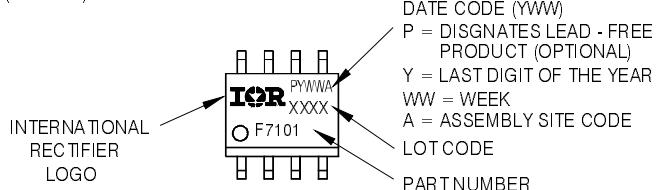
DATE CODE (YWW)
P = DISGNATES LEAD - FREE
PRODUCT (OPTIONAL)
Y = LAST DIGIT OF THE YEAR
WW = WEEK
A = ASSEMBLY SITE CODE

INTERNATIONAL
RECTIFIER
LOGO

IƧR PYWWA
XXXX
F7101

LOT CODE

PART NUMBER

Note: For the most current drawing please refer to IR website at: http://www.irf.com/package/

www.irf.com

SO-8 Tape and Reel

TERMINAL NUMBER 1

12.3 (.484)
11.7 (.461)

FEED DIRECTION

8.1 (.318)
7.9 (.312)
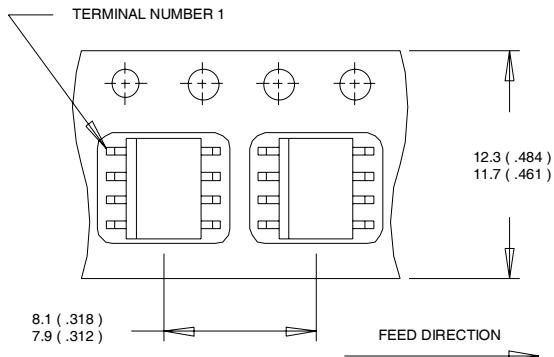
NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
3. OUTLINE CONFORMS TO EIA-481 & EIA-541.

∅ 330.00
(12.992)
MAX.

14.40 (.566)
12.40 (.488)
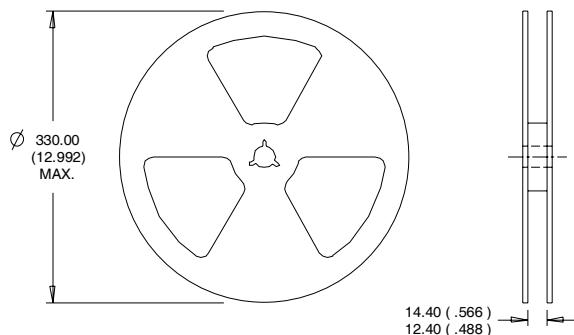
NOTES :
1. CONTROLLING DIMENSION : MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.

Note: For the most current drawing please refer to IR website at: <u>http://www.irf.com/package/</u>

Data and specifications subject to change without notice.
This product has been designed and qualified for the consumer market.
Qualification Standards can be found on IR's Web site.

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